SCHOTTKY BARRIER RECTIFIER

VOLTAGE RANGE: 35 --- 200 V CURRENT: 15.0A

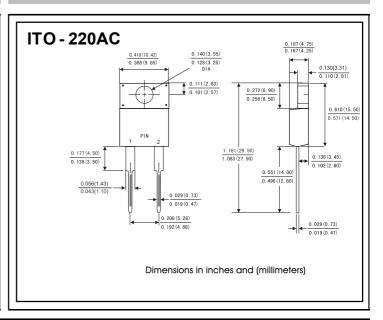
FEATURES

- Metal-semiconductor junction with guard ring

- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications

MECHANICAL DATA

- ♦ Weight: 0.08ounces,2.24 grams



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		Symbols	MBRF 1535	MBRF 1545	MBRF 1550	MBRF 1560	MBRF 15100	MBRF 15150	MBRF 15200	Units
Maximum repetitive peak reverse voltage		Vrrm	35	45	50	60	100	150	200	Volts
Maximum RMS voltage		VRMS	25	32	35	42	70	105	140	Volts
Maximum DC blocking voltage		VDC	35	45	50	60	100	150	200	Volts
Maximum average forward rectified current See Fig. 1		I(AV)	15.0							Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		İfsm	150.0							Amps
Maximum instantaneous forward voltage at 15 A		VF	0.60			D.75	0.85	0. 90	0. 95	Volts
Maximum instantaneous reverse current at rated DC blocking voltage(Note 1)	T _c =25°C		0.2							
	T _c = 125°C	lr	30			50				mA
Typical thermal resistance (Note 2)		$R_{ heta}$ JC	3.0							°C/W
Operating junction temperature range		TJ	-65 to+150							°C
Storage temperature range		TstG	-65 to+150							°C

NOTE: 1. Pulse test:300us pulse width,1% duty cycle.

- 2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
- 3. Thermal resistance junction to ambient

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FIG.1-FORWARD CURRENT DERATING CURVE

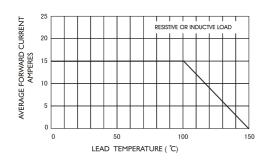


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

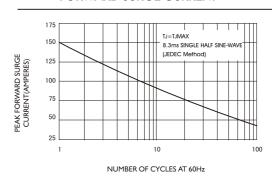


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

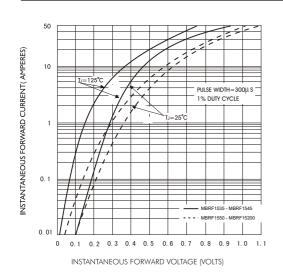


FIG.4-TYPICAL REVERSE CHARACTERISTICS

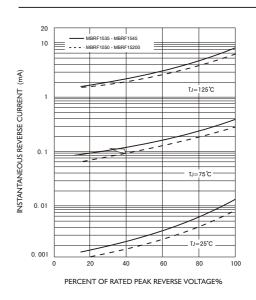


FIG.5-TYPICAL JUNCTION CAPACITANCE

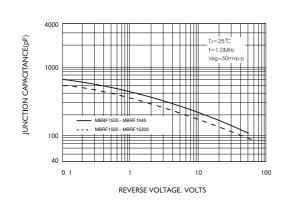
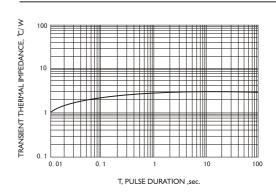


FIG.6-TYPICAL TRANSIENT THERMAL IMPEDANCE



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